

Date: 23.09.2014

Federal Communications Commission Authorization and Evaluation Division 7435 Oakland Mills Road Columbia, MD 21046

Attn: OET Dept.

Ref: FCC Class II Permissive change for FCC ID: WNS-020000007

(Original Grant date: 11/13/2008)

Applicant: Delphi Delco

Dear Examiner,

This is to request a Class II permissive change for FCC ID: WNS-020000007 originally granted on 11/13/2008.

The major changes filed under this application are:

All listed products in the specification description are new revisions of old products (certified in 2008) due to several discontinued components. With respect to the FBDII building block PCB design as well SW is identical with the initial homologation!

All changed FBDII relevant components are drop in replacements and are described in the next pages!

The RF part still remains the same!

If you have any questions regarding this application, please feel free to contact me.

Sincerely yours,

CSA Group Bayern GmbH
Ohmstrasse 1 - 4
94342 Strasskirchen

Name: Thomas Ring

Titel: Teamleader Global Market Access

CSA Group Bayern GmbH

Ohmstrasse 1-4

94342 Strasskirchen, Germany

Supplier Suggestion Change Request # 52932 Date Submitted: 24-Sep-2013

	CON	NTACT INFORMATION	Date Submitted: 24-Sep-201
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	Enter	red By	Owner
Name	Herr Vital	i Michaelis	Herr Vitali Michaelis
Title		err	Herr
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Supplier Suggestion Change Request # 49279

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		Entered Dec		0	
	Nama	Entered By		Owner	
	Name	Sherry Rosselot		Sherry Rosselot	
	Title			Administrator	
	Phone	765-459-5355		765-459-5355	
	Fax	765-455-4031		765-455-4031	
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Supplier Suggestion Change Request # 48319

				Date Submitted : 29-Oct-2012
		CONTACT	INFORMATION	
		Entered By		Owner
	Name	Sherry Rosseld	ot	Sherry Rosselot
	Title	·		Administrator
F	hone	765-459-5355	5	765-459-5355
	Fax	765-455-4031	I	765-455-4031
	Email sh	nerry.rosselot@n	xp.com	sherry.rosselot@nxp.com
Receive Status	Email	N		Υ
Compliant Hitimata Nama	NVD	CENTICONDUCTO	20 N.V	
Supplier Ultimate Name Supplier Ultimate DUNS		SEMICONDUCTOR 55513	3 N.V.	
Supplier Manufacturing Loc		Semiconductors Ne	therlade Supplier N	Manufacturing Location Duns 415097385
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- пррименения дене	,		ART INFORMATION	
		AITEOILDIA	ART INI ORIMATION	
Is this	a pass-thru or direc	ct ship product? 🧿	No OYes	
Ship To Location(s) DA31,	DAT3, Hungary, Gda	nsk, DA26, Megam	os, fuba, Texton & Braç	ga
-	Electronics & Safety			
Region North A	merica		Commodity Gro	oup Electrical
Delphi Part # / PO #(for	Revision		Drawing No.	. Part / Project Name
Indirect)				
28136407	Α		Unknow	Unknown
00110700		Addition	nal Parts	
28148503	Α		Unknown	Unknown
	Supplier Part #	Supp	lier Part Name	
	TJA1021T/20/	C LINT	ransceiver SO8	
	Addi	tional Part Numbe	rs	
	TJA1021T/10/	C LIN T	ransceiver SO8	
Product Application	Unknown			
Delphi Buyer Name	May Leong		Product Engineer	
Delphi Buyer Phone	Unknown	/ Ii- D-If-	Delphi Engineer Pl	hone Unknown
Delphi SQE / AQE Name Is this an Emergency?		er / Loris Rolfe		
is this till Emergency !	10 0 103			
Other Delphi Contact	<u>Titl</u>	<u>le</u>	<u>Name</u>	<u>Phone</u>
1 2				
2		DEFINE CH	ANGE REQUEST	
		DEI INC CIT	ANGL KLQULST	
			<u>Title</u>	
		Quality Improveme	nts to TJA1021T LIN T	Transceiver
Detail Description of Change		scoes will have the f	ollowing quality improv	vements made: - Process update to PA100TMX04 using HDP
passivation - Mould compound	rs out of ABCD-3 pro I (Sumitomo EME621	0 to Nitto GE7470)	Die attach material (A)	Ablebond 8390P to Henkel QMI-519) - Roughened top side
leadframe (already used in oth	er transceivers, refer	ence SCR30756) -	Wafer thickness (380ui	im to 280um) - Bondwire diameter and material (25um AuBe to
				at to change submission - Type descritpion will also change:
TJA1021T/10/C to TJA1021T/	10/CM and 1JA1021	1/20/C to 1JA10211	/20/CIVI - No change to	o the exisiting NAP datasneet.
Reason for Change These changes are a result of	ongoing quality impro	ovements and indus	strial standardizations a	and not from any underlying quality issue
Reference PCR Number :	origoning quanty impro	overnorne and induc	and oldinadial Editions a	and not nom any anaonymy quanty locate
Troioronos i orritambor :				
		CHAN	GE IMPACT	
		Types of	Improvement	
□ Coat	☑ Quality	П 0°	livory	☐ Logistics
Cost	Quality		livery	
Consumer Appeal		Support	uipment Upgrade	Software Enhancement
		Α	Affects	
Appearance	☐ Function			☐ Location change
	☐ Packaging		☐ Customer Interfa	
Impact Change will have	_		_	
A more robust part. Should ha	ve no negative impac	ct to customer.		
·	<u> </u>			
Estimated Implementation Lead Time	e:	1 Months		
Requested Disposition Date :	: D	31-Mar-2013	Sample Parts to De	
Component Data / Test Data to Delph	ы ру :	29-Oct-2012	Desired Date for Pr	roduction at Supplier Facility: 31-Mar-2013

Supplier Suggestion Change Request # 48318

				Date Submitted: 29	
		CONTACT INFORM	ATION		
		Entered By		Owner	
		Entered By		Owner Shorry Possolet	
	Title	nerry Rosselot		Sherry Rosselot Administrator	
		65-459-5355		765-459-5355	
		65-455-4031		765-459-5555 765-455-4031	
		osselot@nxp.com		sherry.rosselot@nxp.com	
Receive Status		N		Υ	
1000	Lilian	14		•	
Supplier Ultimate Name	NXP SEMIC	CONDUCTORS N.V.			
Supplier Ultimate DUNS	414955513				ļ
Supplier Manufacturing Lo	cation Name NXP Semico	ondcutors Netherlands	Supplier Manufac	turing Location Duns 415097385	į
Supplier Manufacturing Loc	cation City Nijmegen		Supplier Manufac	turing Location State	ļ
Supplier Manufacturing Loc	cation Country NETHERLA	NDS			
	AF	FECTED PART INFO	RMATION		
	s a pass-thru or direct ship	product? No O	′es		
Ship To Location(s) Fuba					
·	i Electronics & Safety		_		
Region Europ	е	Со	mmodity Group	Electrical	
Delphi Part # / PO #(for	Revision		Drawing No.	Part / Project Name	
<u>Indirect)</u>					ļ
28086447	A		Unknown	Unknown	ļ
		Additional Parts			ļ
28117864	A		Unknown	Unknown	
	Complier Bort #	Complier Port I	lama		
	Supplier Part #	Supplier Part N			
	PQJ7980AHN/C0CH	LoPSTer 1.2	25		
		Part Numbers			
	PQJ7980AHN/C0DL	LoPSTer 1.2	25		
Product Application	Unknown				
Delphi Buyer Name	Unknown	Produ	ct Engineer Name	Unknown	
Delphi Buyer Phone	Unknown		Engineer Name	Unknonw	
Delpili Buyer Frione	Ulkilowii	Deibiii	Engineer Frione	UNKHONW	
Delphi SOF / AOF Name	Rurkhard Exper				
Delphi SQE / AQE Name Is this an Emergency?	Burkhard Exner				
Is this an Emergency?	No O Yes				
Is this an Emergency? Other Delphi Contact	No O Yes		<u>Name</u>	Phone	
Is this an Emergency? Other Delphi Contact 1	No O Yes		<u>Name</u>	<u>Phone</u>	
Is this an Emergency? Other Delphi Contact	No O Yes <u>Title</u>	DEFINE CHANCE DE		<u>Phone</u>	
Is this an Emergency? Other Delphi Contact 1	No O Yes <u>Title</u>	DEFINE CHANGE RE		<u>Phone</u>	
Is this an Emergency? Other Delphi Contact 1	No O Yes <u>Title</u>	DEFINE CHANGE RE <u>Title</u>		<u>Phone</u>	_
Is this an Emergency? Other Delphi Contact 1	No		QUEST		_
Other Delphi Contact 1 2 Detail Description of Change	No Yes Title Quality	Title Improvements to LoP	QUEST STer 1.25 PQJ7980A	HN	_
Other Delphi Contact 1 2 Detail Description of Change NXP is making the following of the contact of the conta	No Yes Title Quality ge Proposal design, manufacturing and tes	Title Improvements to LoPast changes to the listed	QUEST STer 1.25 PQJ7980Al I types: -New passiva	HN tion stack (HDP stack) This will give an incre	
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Other Delphi Contact 1 2 Detail Description of Chang NXP is making the following of mechanical robustnessWafa against moistureMoisture S regulator thresholds which with SAW filter (1.25 only) -ESD in PQJ7980AHN/COCH, once question of the contact of the	Quality Quality Proposal design, manufacturing and tele ercoating change which will a lensitivity Level will change fr Il improve power output contr nprovement—> Specification i ualified will be PQJ7980AHN/ made for a more robust part, I	Title Improvements to LoP st changes to the listed also improve mechanic om MSL-3 to MSL-2a olPA and VCO isola upgrade -DC testing P /COIH -New type describut not for any underly CHANGE IMPAC	QUEST STer 1.25 PQJ7980Al I types: -New passiva al robustnessImpro- EMC (clock spurs) to tion improvement which A which will give test ription for PQJ7980Al ing quality issue.	HN tion stack (HDP stack) This will give an increved leadframe version. This will increase rol improve EMC performance at clock input -/ch will improve robustness at TX application coverage improvement -New type descriptic HN/C0DL, once qualified will be PQJ7980AH	oustness Adjust PA with on for
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